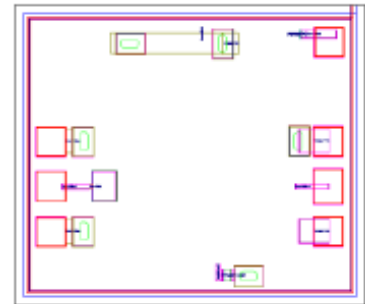


AMT1213
7 – 13GHz Low Noise Amplifier Chip



Key Features :

- Frequency range : 7 – 13GHz
- Typical gain : 8.5dB
- Input standing wave : 1.3
- Output standing wave : 1.1
- Noise figure : 2.2dB
- P-1 : 12dBm @ +4.1V/18mA
- Chip dimensions : 1.175mm x 1mm x 0.1mm
- Applications : wireless communication, transceiver module, radio telecommunication etc.

Description :

AMT1213 chip is a Gallium Arsenide (GaAs) high performance Low Noise Amplifier, it covers 7 – 13GHz frequency range. It uses +4.1V single voltage operation, noise figure is 2.2dB, and 8.5dB typical gain. This chip is designed with ground through metal vias on the back technology. All chip products p are 100% RF tested.

Absolute Maximum Ratings (Ta = 25°C)

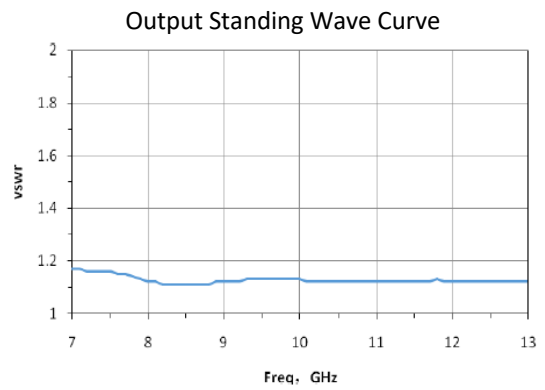
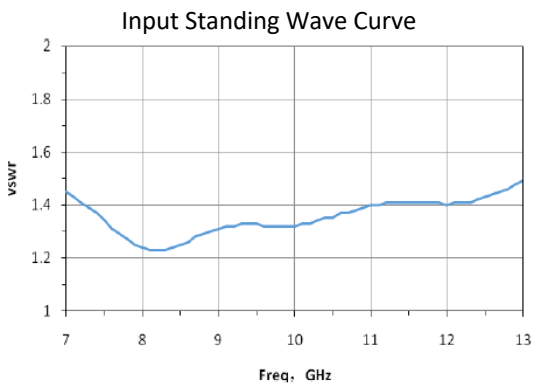
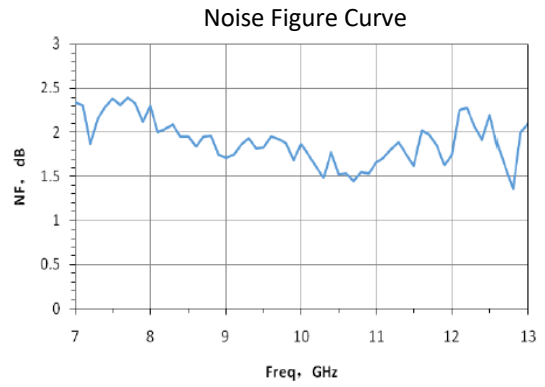
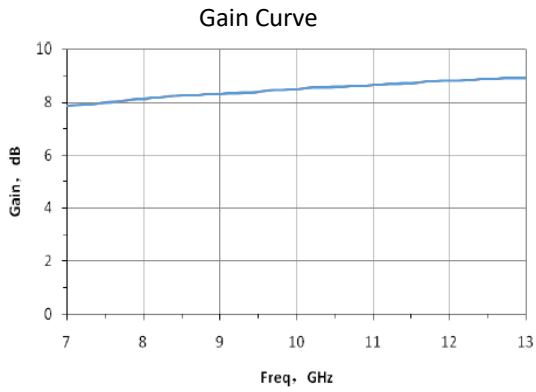
Symbol	Parameter	Value	Remark
Vd	Drain Voltage	+7V	
Pin	Input Signal Power	17dBm	
Tch	Operating Temperature	150°C	
Tm	Sintering Temperature	310°C	30s, N ₂ protection
Tstg	Storage Temperature	-65 ~ +150°C	

[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

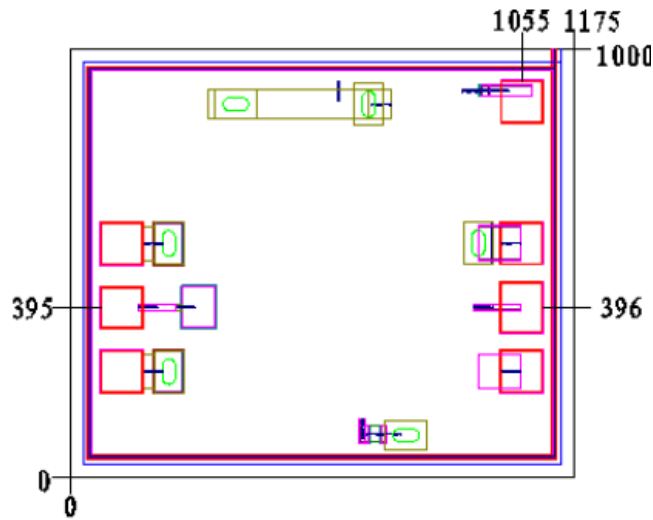
Electrical Characteristics (Ta = 25°C)

Symbol	Parameter	Test Conditions	Value			Unit
			Min	Typical	Max	
G	Gain	Vd = +5V F : 7 ~ 13GHz	-	8.5	-	dB
NF	Noise Figure		-	2.2	3	dB
Id	Static Current		-	18	-	mA
VSWR_in	Input Standing Wave		-	1.3	-	-
VSWR_out	Output Standing Wave		-	1.1	-	-
P-1	Output Power at 1dB point		-	12	-	dBm

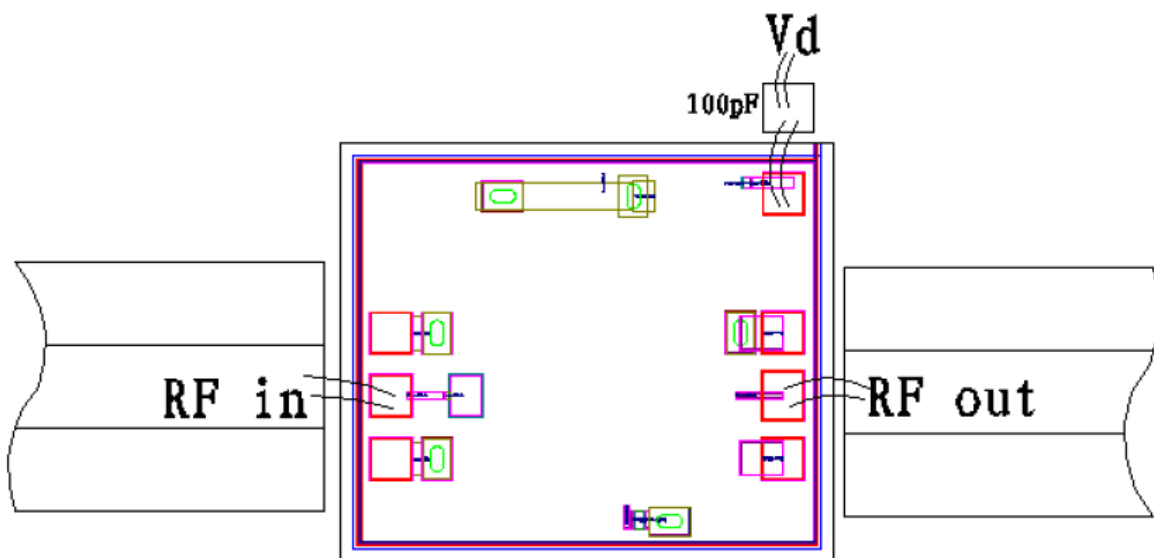
Typical Performance



Chip Dimensions (Unit : μm)



Chip Layout Diagram



Pad Definition

Symbol	Function	Dimension	Equivalent Circuit
RF_in	RF signal input port, connecting to external 50Ω system. no need to add DC blocking capacitor.	$100*100\mu\text{m}^2$	
RF_out	RF signal output port, connecting to external 50Ω system, no need to add DC blocking capacitor.	$100*100\mu\text{m}^2$	
Vd	Amplifier bias, need to connect external 100pF capacitor.	$100*100\mu\text{m}^2$	

Please see Appendix A for details.